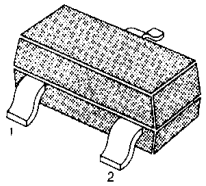
KST55/56 PNP EPITAXIAL SILICON TRANSISTOR

DRIVER TRANSISTOR

SOT-23



1. Base 2. Emitter 3. Collector

ABSOLUTE MAXIMUM RATINGS (T_A=25℃)

Characteristic	Symbol	Rating	Unit
Collector Base Voltage	V_{CBO}		
:KST55		-60	V
:KST56		-80	V
Collector-Emitter Voltage	V_{CEO}		
:KST55		-60	V
:KST56		-80	V
Emitter-Base Voltage	V_{EBO}	-4	V
Collector Current	I_C	-500	mA
Collector Dissipation	P_C	350	mW
Storage Temperature	T_{STG}	150	℃
Thermal Resistance junction to Ambient	R_{TH}(j-a)	357	℃/w

• Refer to KSP55 for graphs

ELECTRICAL CHARACTERISTICS (T_A=25℃)

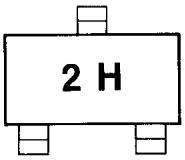
Characteristic	Symbol	Test Conditions	Min	Max	Unit
★Collector-Emitter Breakdown Voltage	BV_{CEO}	I_C= -1mA, I_B=0			
:KST55			-60		V
:KST56			-80		V
★Collector-Base Breakdown Voltage	BV_{EBO}	I_E= -100㎂, I_C=0	-4		V
Collector Cut-off Current	I_{CBO}	V_{CE}= -60V, I_E=0		-0.1	㎂
Collector Cut-off Current	I_{CEO}				
:KST55		V_{CE}= -60V, I_B=0		-0.1	㎂
:KST56		V_{CE}= -80V, I_B=0		-0.1	㎂
DC Current Gain	h_{FE}	V_{CE}= -1V, I_C= -10mA	50		
		V_{CE}= -1V, I_C= -100mA	50		
Collector-Emitter Saturation Voltage	V_{CE} (sat)	I_C= -100mA, I_B= -10mA		-0.25	V
Base-Emitter On Voltage	V_{BE} (sat)	V_{CE}= -1V, I_C= -100mA		-1.2	V
Current Gain Bandwidth Product	f_T	V_{CE}= -1V, I_C= -100mA f=100MHz	50		MHz

★Pulse Test: PW≤ 300㎲, Duty Cycle≤ 2%

MARKING CODE

TYPE	KST55	KST56
MARK	2H	2G

Marking



SAMSUNG ELECTRONICS